



- [54] **INTEGRATED SENSOR WITH FRAME MEMORY AND PROGRAMMABLE RESOLUTION FOR LIGHT ADAPTIVE IMAGING**
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- [73] Assignee: **California Institute of Technology**, Pasadena, Calif.
- [21] Appl. No.: **08/867,835**
- [22] Filed: **Jun. 3, 1997**

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- [51] Int. Cl.⁶ **H01J 40/14**
- [52] U.S. Cl. **250/208.1**; 348/317
- [58] Field of Search 250/208.1; 348/317-319, 348/302-304

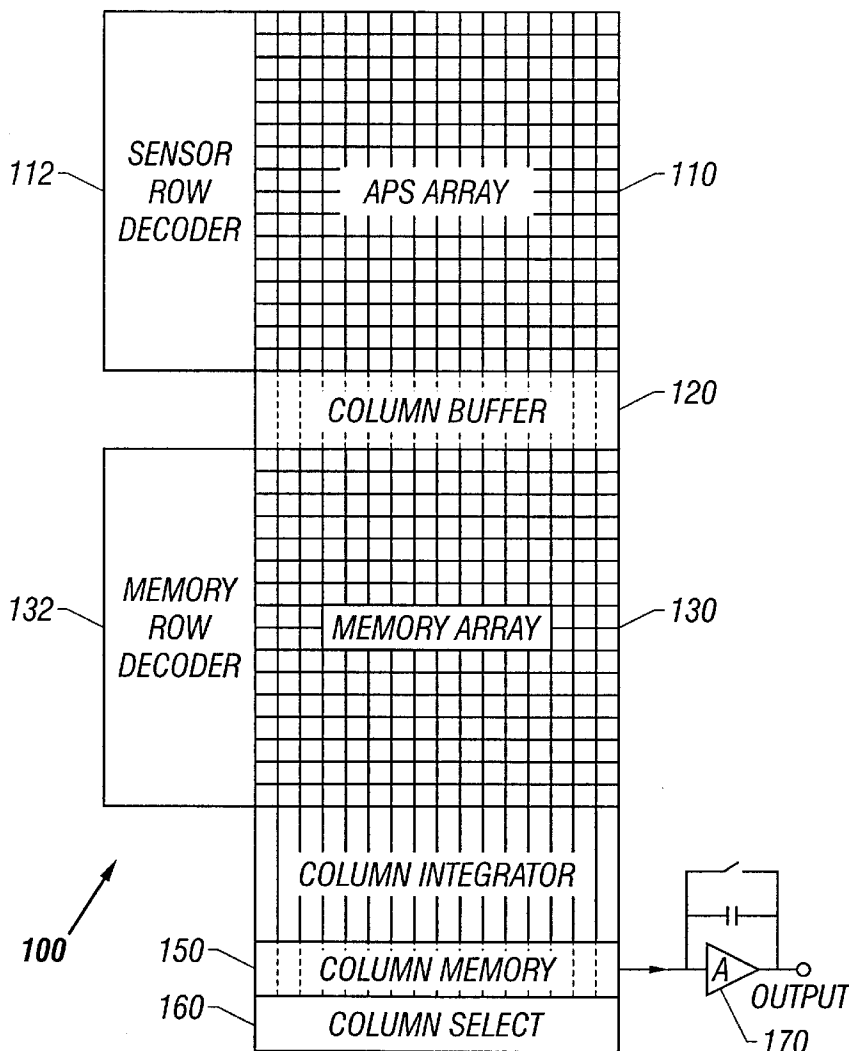
- [56] **References Cited**
- U.S. PATENT DOCUMENTS
- 5,402,171 3/1995 Tagami et al. 250/208.1
- 5,471,515 11/1995 Fossum et al. 377/60

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[57] **ABSTRACT**

An image sensor operable to vary the output spatial resolution according to a received light level while maintaining a desired signal-to-noise ratio. Signals from neighboring pixels in a pixel patch with an adjustable size are added to increase both the image brightness and signal-to-noise ratio. One embodiment comprises a sensor array for receiving input signals, a frame memory array for temporarily storing a full frame, and an array of self-calibration column integrators for uniform column-parallel signal summation. The column integrators are capable of substantially canceling fixed pattern noise.

20 Claims, 9 Drawing Sheets



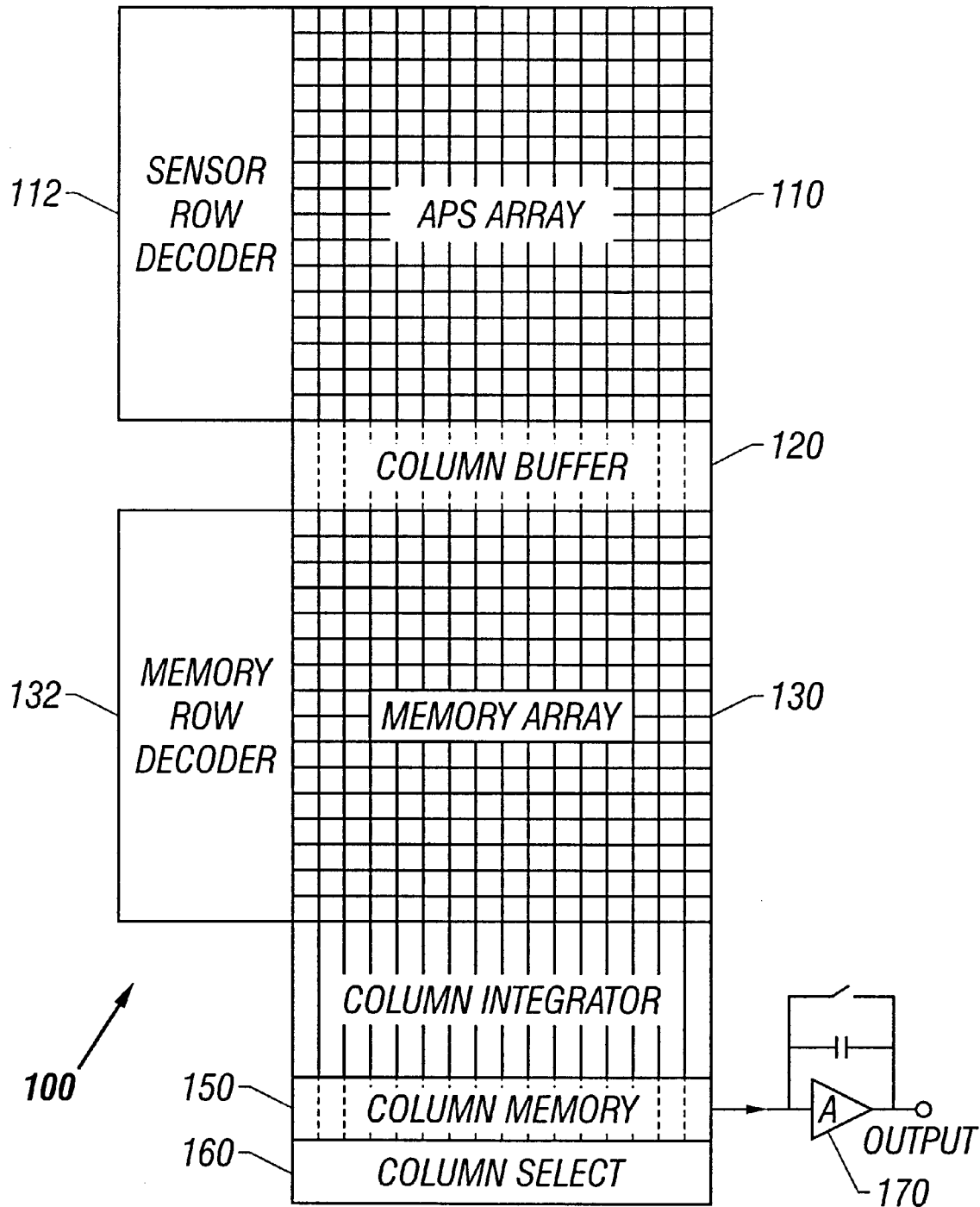
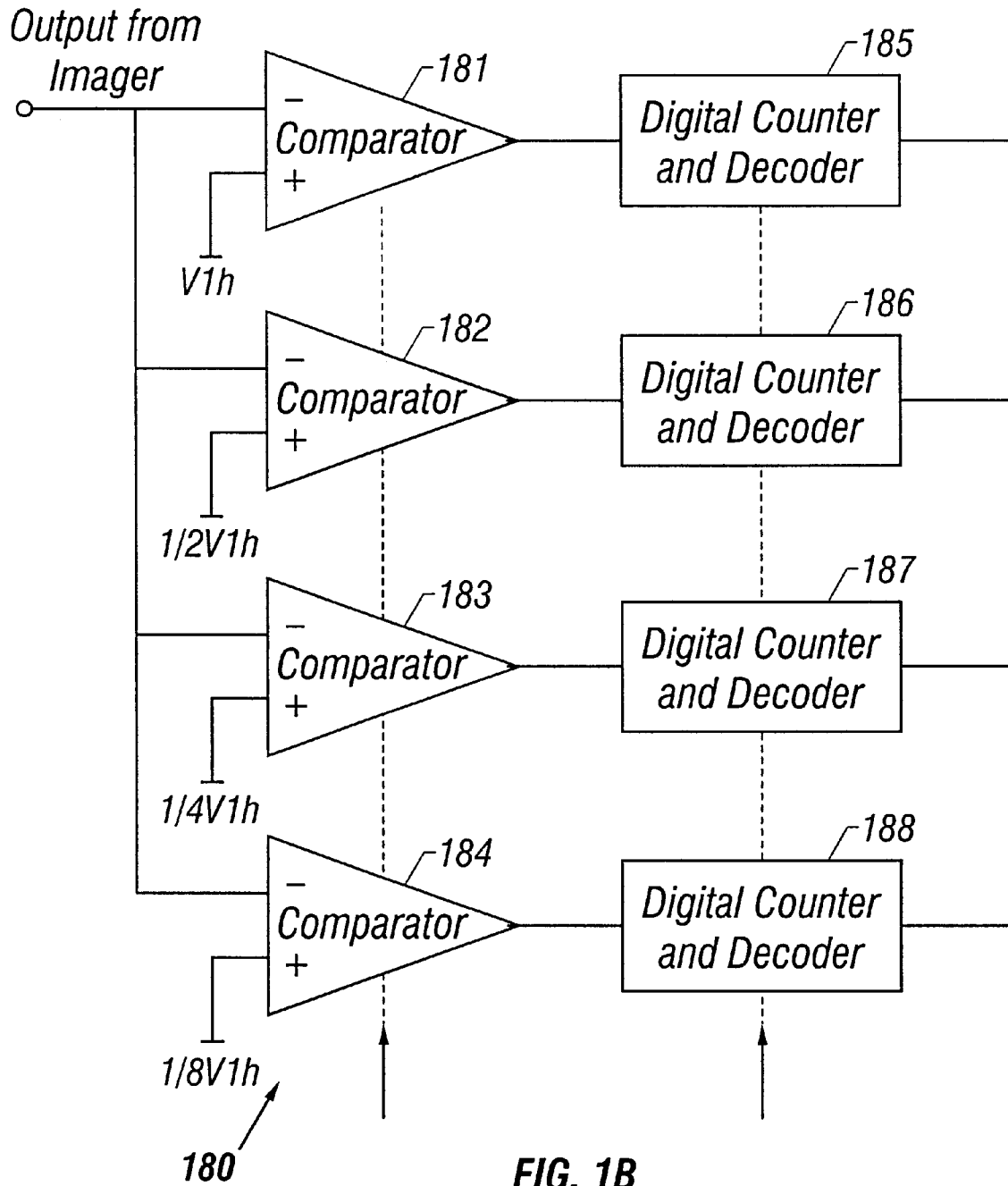


FIG. 1A



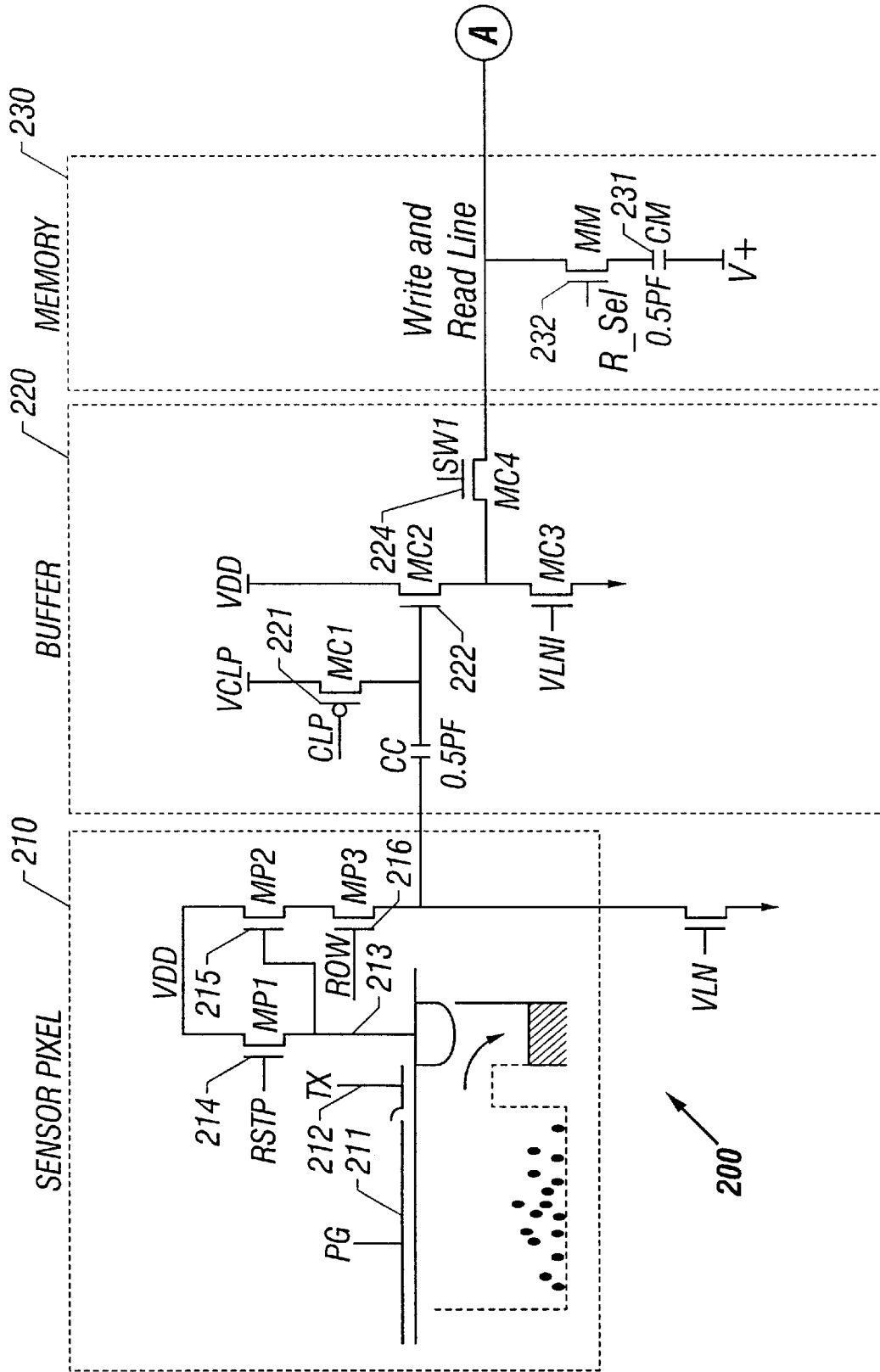


FIG. 2A

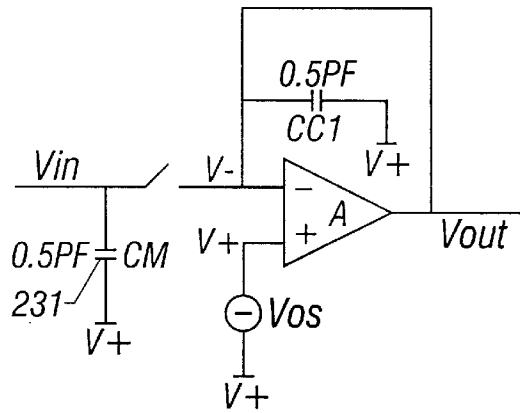


FIG. 3A

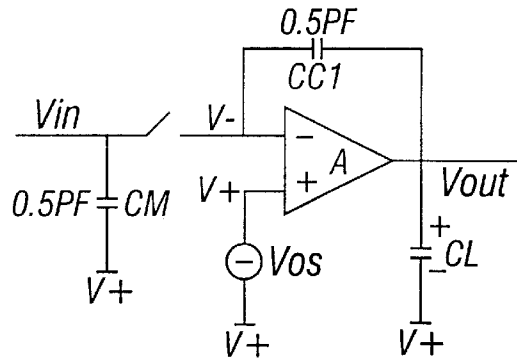


FIG. 3B

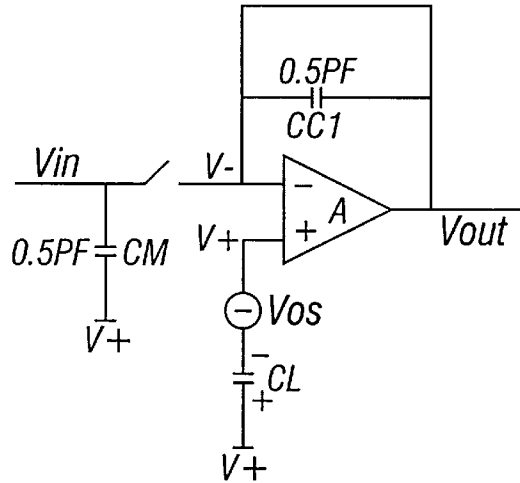


FIG. 3C

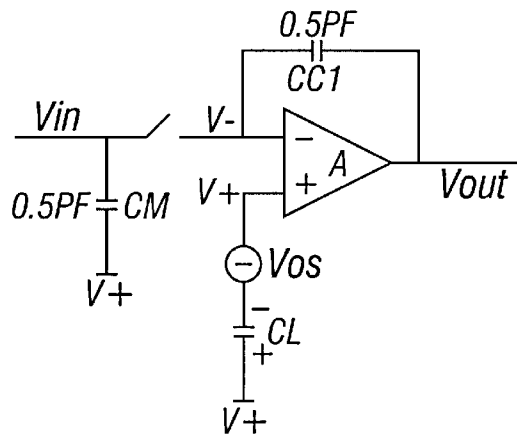
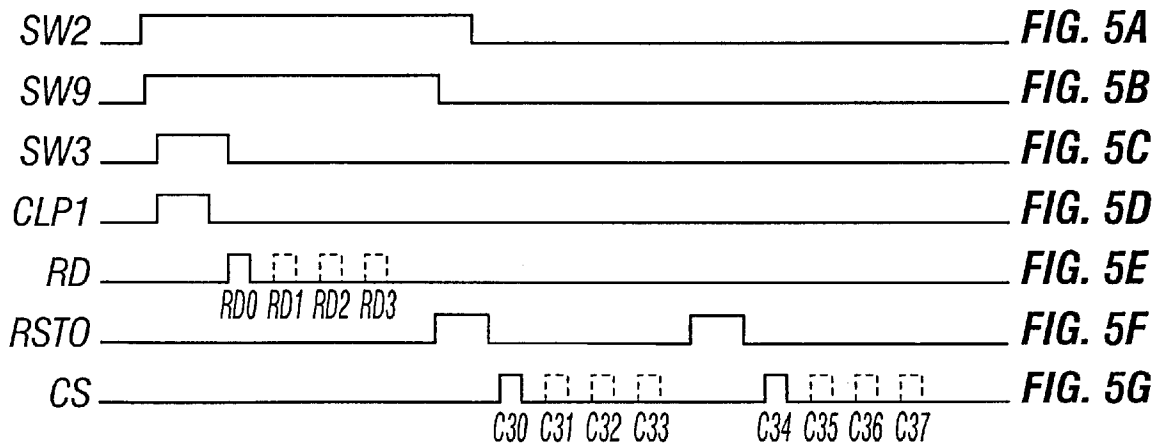
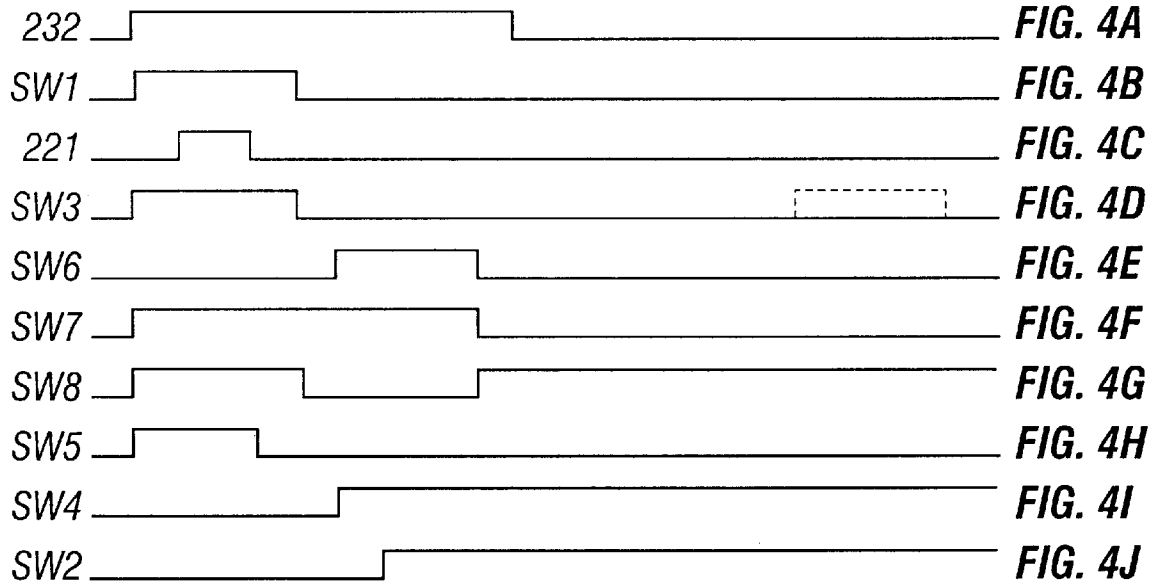


FIG. 3D



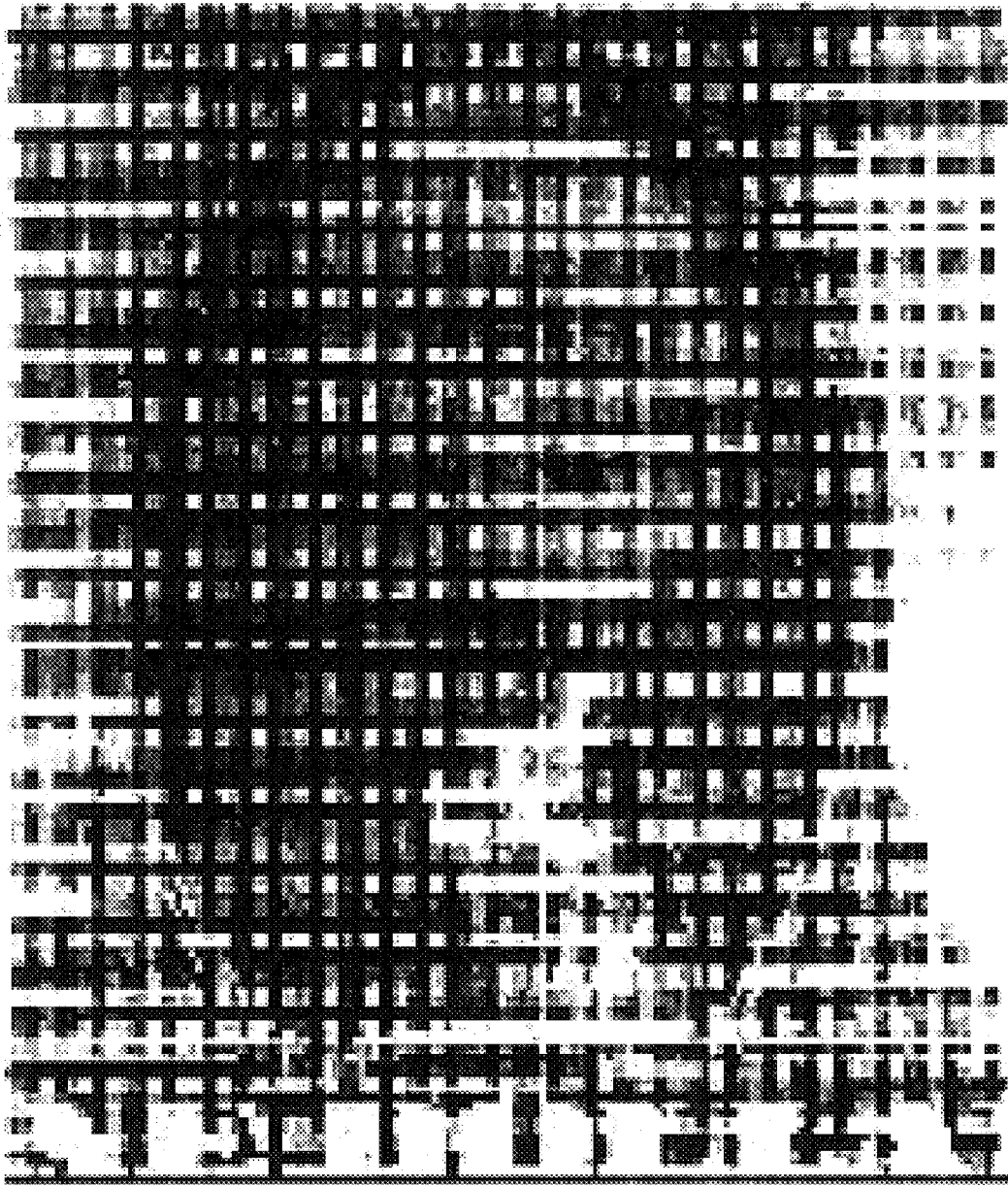


FIGURE 6

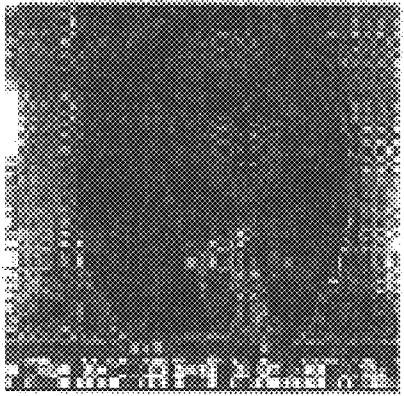
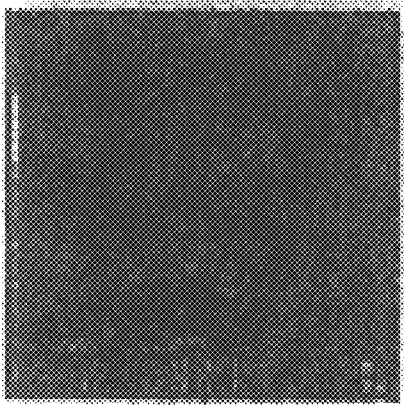


Figure 7A

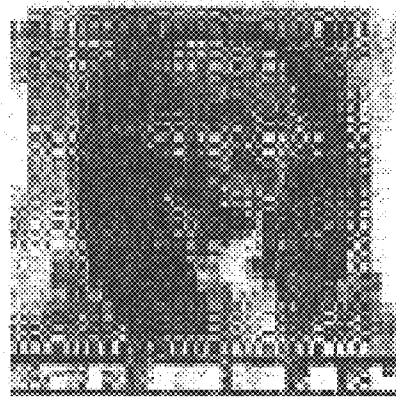
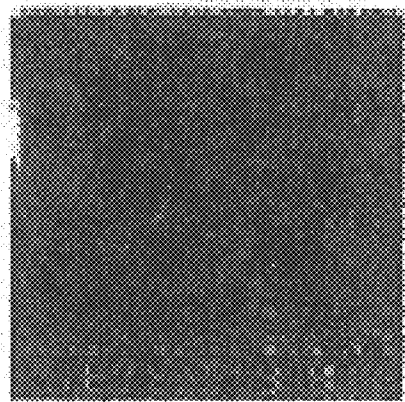


Figure 7B

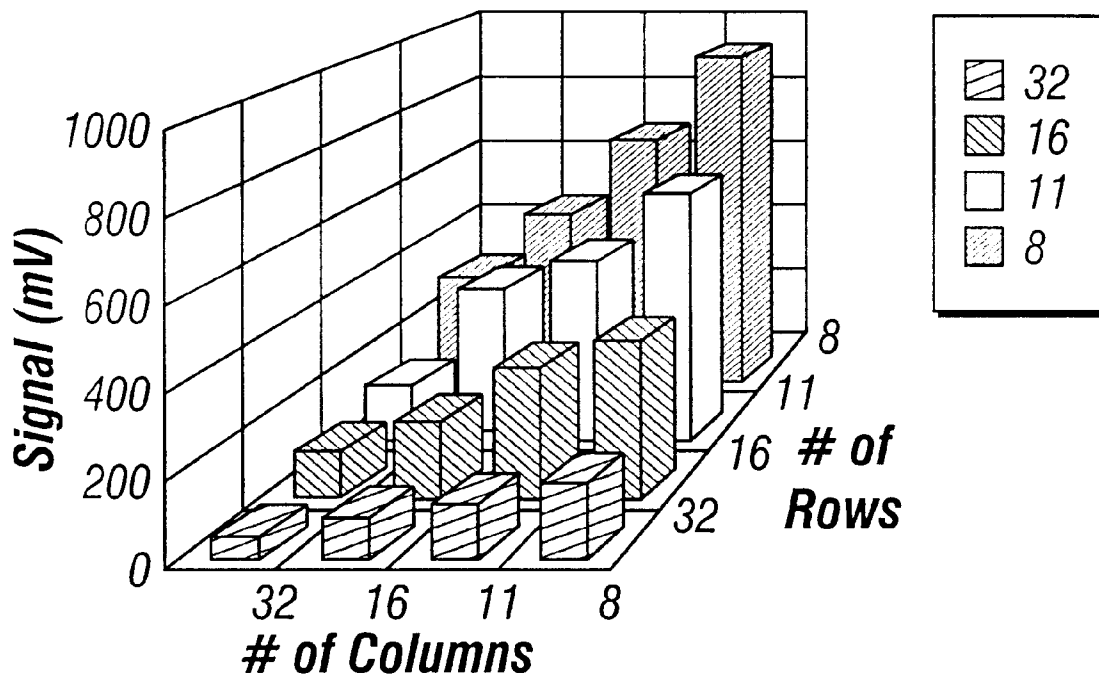


FIG. 8A

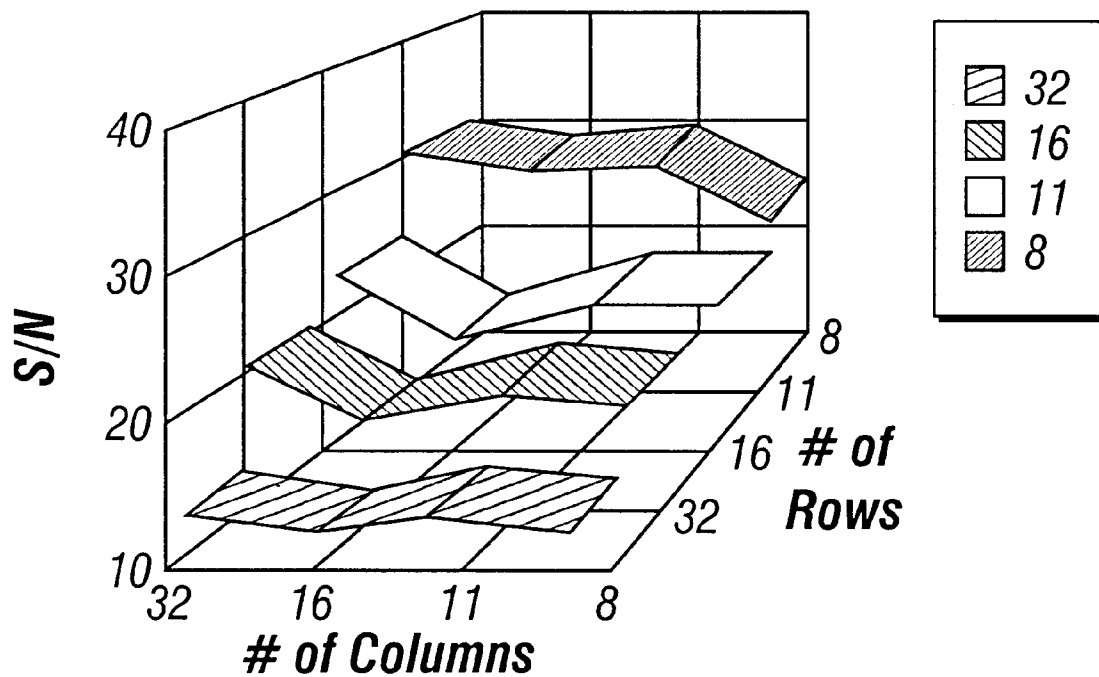


FIG. 8B

**INTEGRATED SENSOR WITH FRAME
MEMORY AND PROGRAMMABLE
RESOLUTION FOR LIGHT ADAPTIVE
IMAGING**

This application claims the benefit of the U.S. Provisional application No. 60/030,646, filed on Nov. 12, 1996, the entirety of which is incorporated herein by reference.

ORIGIN OF THE INVENTION

The invention described herein was made in the performance of work under a NASA contract and is subject to the provisions of Public Law 96-517(35 U.S.C. 202) in which the Contractor has elected to retain title.

FIELD OF THE INVENTION

The present invention relates to semiconductor image sensors, and more specifically, to an imaging device with on-chip frame memory suitable for imaging applications under low lighting conditions.

BACKGROUND OF THE INVENTION

An active pixel sensor ("APS") is a light sensing device with sensing circuitry inside each pixel. Each active pixel includes a light sensing element and one or more active transistors within the pixel itself. The active transistors amplify and buffer the signals generated by the light sensing elements in the pixels. In comparison with the widely used charge coupled devices (CCDs), an APS device has a number of unique and beneficial features. These features include the ability to receive and process input signals with the active pixels without the charge transfer process inherent in CCDs. An APS device is also compatible with CMOS processes.

Elimination of the charge transfer allows APS devices to have a higher readout rate than those of CCDs and also to maintain their performance as the array size increases. Compatibility with CMOS processes allows many signal processing functions and operation controls to be integrated on an APS chip. Use of CMOS circuitry with APS devices also reduces cost of manufacturing and power consumption. Moreover, the active pixels of APS devices allow non-destructive readout and random access.

One configuration of APS sensors is disclosed in U.S. Pat. No. 5,471,515 by Fossum et al., the disclosure of which is incorporated herein by reference. Such an image sensor typically operates at a constant finite frame rate with a constant signal integration time. The frame rate and the integration time are often preset for normal operating conditions under which illumination is usually sufficient. The performance of such a conventional image sensor suffers when the illumination is below the typical level to which the image sensor is configured. Since the frame integration time is usually preset for a predetermined normal light condition, little signal may be collected under a low light condition with an illumination level below the predetermined normal light condition. Conversely, too much signal may also be collected when input light level is higher than the predetermined level. Thus, a clear image of a target can be difficult to obtain under different light conditions.

One conventional technique to circumvent this problem under low light conditions uses averaging the signals from a plurality of neighboring pixels in order to reduce the noise level. This averaging technique improves the signal-to-noise ratio of the image sensor. The averaging process, however,

also reduces the image resolution. Suppose a patch of $N \times N$ pixels are averaged, the signal-to-noise ratio is then improved by a factor of $N^{1/2}$ while the resolution is reduced by a factor of N . One limitation of this averaging technique is that the signal level achieved from averaging essentially remains unchanged compared to the signal levels of the selected neighboring pixels. Additional signal amplification is thus needed to obtain a brighter image.

SUMMARY OF THE INVENTION

The present disclosure describes a new approach to the above-addressed problem in image sensors. Instead of averaging signals from selected neighboring pixels, signals of the neighboring pixels are preferably added together according to the present invention. In contrast to the prior-art method, a sensing device in accordance with the invention increases both the signal and the noise with different factors so that the overall signal-to-noise ratio improves by the signal processing. The total signal can be increased by a factor of N^2 for a square patch of $N \times N$ neighboring pixels. The total noise comparatively increases by a factor of $(N)^{1/2}$. This allows the signal-to-noise ratio to increase by a factor of $(N)^{1/2}$. One of the advantages of the present invention is significant enhancement in both the signal level and the signal-to-noise ratio.

An APS image sensor with an adaptive resolution based on the above new technique is disclosed herein. One embodiment comprises an APS array for receiving input signals, a column buffer array for generating photo-induced electrical signals indicative of the input signals, a frame memory array for storing signals from the APS array, a column integrator array for signal summation for rows selected by a row decoder, and an output integrator for signal summation for columns selected by a column selector.

One aspect of the APS image sensor of the present invention allows increasing the magnitude of the output image with a reduced spatial resolution under low illumination.

Another aspect of the APS image sensor of the present invention allows dynamically adjusting the image resolution and maintaining the output signal level above a preset level according to the conditions of a target object.

Still another aspect is a self-calibration feature of the column integrator array that allows substantial elimination of the column-wise fixed pattern noise in the signals both prior to and during the signal integration.

BRIEF DESCRIPTION OF THE DRAWINGS

These and other aspects and advantages of the present invention will become more apparent in light of the following detailed description, as illustrated in the accompanying drawings, in which:

FIG. 1a is a schematic illustrating a preferred chip architecture of an APS image sensor in accordance with the present invention.

FIG. 1b is a block diagram showing an exemplar 4-bit command word generator for light adaptive resolution adjustment, which is a part of a resolution control circuit.

FIG. 2 shows a signal chain of the APS image sensor of the present invention including the active pixel layout, the column buffer circuit, the frame memory circuit, the column integrator circuit, and the output integrator circuit.

FIGS. 3a, 3b, 3c, and 3d show the equivalent circuit diagram of the column integrator during (a) calibration reset, (b) calibration sampling, (c) reset prior to integration, and (d) integration.

FIGS. 4a, 4b, 4c, 4d, 4e, 4f, 4g, 4h, 4i, and 4j show various electrical signals of an APS image sensor of the present invention in the time domain in a preferred operation mode for calibrating the fixed pattern noise.

FIGS. 5a, 5b, 5c, 5d, 5e, 5f and 5g depict various electrical signals of the preferred APS image sensor in the time domain in an example of programmable resolution readout process.

FIG. 6 shows an image with full resolution taken with a tested image sensor in accordance with the present invention.

FIGS. 7a–7b and 8a–8b show signal enhancement by changing the kernel size in a tested image sensor in accordance with the present invention.

DETAILED DESCRIPTION OF THE INVENTION

The description of the present invention will use a CMOS APS device as an example for implementation. However, it should be understood that the method and design can also be implemented in other active pixel sensors, and may be usable in other image-acquiring systems.

A chip construction **100** of the APS image sensor in accordance with the invention is shown in FIG. 1a. An active pixel array **110** with a plurality of active light-sensing pixels for receiving radiation from an target object is connected to a sensor row decoder **112** which operates to address rows of APS pixels. A column buffer array **120** has multiple buffer cells with each corresponding to a column of the APS array **110**. Each column buffer cell receives signals from an addressed active pixel of the APS array **110** to generate a signal. That signal is induced only based on the received radiation in that active pixel.

A frame memory array **130** has memory cells with an one-to-one correspondence with the active pixels of the APS array **110**. The radiation-induced signals of a full frame image captured by the APS array **110** are stored in an on-chip frame memory **130** prior to the signal integration. This on-chip frame memory **130** provides a convenient vehicle for light-adaptive imaging and can be further used in a time delay integration (“TDI”). A memory row decoder **132** is used to randomly access and select rows of memory cells in the frame memory **130**.

A column integrator array **140** performs parallel signal summation for different rows of cells in the frame memory **130**. The summed signals are stored in a column memory array **150** which usually includes a series of capacitors corresponding to the rows of the frame memory **130**. A column select circuit **160** is used to randomly access and select cells in the column memory **150** (equivalently, columns of the frame memory **130**) to be added with one another by an output integrator **170**.

The APS chip **100** also includes a control circuit (not shown) for controlling the operation of the image sensor including operation of the clock generator circuits for synchronization, resolution adjustment, and the operation of the readout circuits.

The resolution of the output image can be determined by programmably changing the summation kernels in the frame memory **130** with the memory row decoder **132** and the column select **160**. This operation can be controlled by a resolution control circuit (see FIG. 1b). The resolution control circuit monitors the magnitude of the received signal level from the APS array **110** so that the size of the summation kernel can be determined for a subsequent signal processing.

A threshold circuit with different levels of threshold values is used to determine the illumination condition and thereby adjust the kernel size. The smallest kernel size is one pixel for the highest resolution under good illumination. The resolution control circuit automatically increases the kernel size if the input signal decreases.

FIG. 1b shows a 4-bit command word generator **180** as one embodiment of the resolution control circuit. This circuit is used to adjust the resolution based on one frame of data by controlling the operation of the addressing circuit of the imaging array.

The command word generator **180** includes a plurality of comparators **181–184** connected in parallel so that all receive the imager output. Each of the comparators has a different threshold level. FIG. 1b shows four comparators **181, 182, 183,** and **184** with threshold levels V_{th} , $0.5 V_{th}$, $0.25 V_{th}$, and $0.125 V_{th}$, respectively. Each comparator is connected to an associated digital counter and decoder **185–188** to produce one of the bits of the 4-bit word. One way to determine a bit of a comparator is to assign “1” to a comparator if the signal is higher than the threshold value and “0” if the signal is lower than the threshold value. This allows the circuit to achieve $2^4=16$ different resolutions based on the 4-bit word.

In one mode for the command word generator **180**, one pixel data sampled at the output of the sensor array is compared with four binary scaled threshold voltages. Referring back to FIG. 1a, the data may be sampled from the sensor array **110** or the frame memory array **130**. The signal in each pixel of a captured frame is sampled and evaluated by the command word generator **180** in order determine the summation kernel size for a subsequent frame.

One extreme case is that the signals from more than half the number of the pixels are higher than V_{th} . Then the 4-bit word generated by the circuit **180** for each of these bright pixels is 1111. The control circuit may be programmed to indicate this case as a satisfactory illumination for the highest resolution depending on the requirements of an application. The resolution control circuit then configures the kernel size to be 1, i.e., no signal summation is performed and the resolution is the highest.

Conversely, if the signals from more than half the number of the pixels are lower than the lowest threshold level (e.g., $0.125 V_{th}$ in FIG. 1b), the 4-bit word is 0000 for each of these pixels. The control circuit may be programmed to indicate this case as a poor illumination. The resolution control circuit accordingly is controlled to set the kernel size to a preset maximum value and a predetermined lowest resolution will be used in the next frame readout. In adjusting the resolution, this implementation has one frame latency.

FIG. 2 shows a preferred signal chain **200** for the preferred chip architecture of FIG. 1a. It should be noted that the capacitance values in the FIG. 2 only represent typical values of an embodiment and should not be construed as limitations of the invention. An active pixel **210** includes a photogate **211**, a transfer gate **212**, an output floating diffusion **213**, a reset transistor **214**, a gate source follower **215**, and a row selection transistor **216**. Other design of the active pixel can also be used. An AC-coupled follower buffer **220** represents a column buffer cell in the column buffer array **120** shared by a column of active pixels in the APS array **110**. The input of the buffer cell **220** is clamped to a finite voltage VCLP by a clock CLP as the active pixel **210** resets and is released as the active pixel **210** gives out a signal. Thus, the buffer cell **220** converts consecutively-sampled

APS sensor reset level and signal level into an optically induced signal that is exported to a memory cell **230** of the frame memory **130**. Many aspects of the APS pixel **210** and the buffer cell **220** are disclosed in the above-incorporated reference, U.S. Pat. No. 5,471,515.

The memory cell **230** includes a memory capacitor **231** and a switch transistor **232**. Circuit **240** is a switched-capacitor integrator and represents one cell in the column integrator array **140** with input from cells of a row in the frame memory **130** (e.g., memory capacitor **231**). A folded-cascade operational amplifier can be used as amplifier **240a**; though other amplifiers may also be used. A column signal memory capacitor **260** (CMC), representing one cell in the column memory **150**, is AC coupled to the integrator output port as a load when signals are integrated. An output integrator **170** includes a compensated two-stage opamp **172** with a large source-follower buffer to drive off-chip load at the video rate.

A typical CMOS APS sensor uses column-wise source follower buffers, e.g., source follower **215** in the active pixel **210** and the transistor **222** in the column buffer cell **220** shown in FIG. **2**, to sample signals onto the memory capacitors. A column-wise spatial fixed pattern noise (FPN) may be introduced by such sampling due to the threshold mismatch in the source follower transistors. The column integrator **240** in each column is designed to achieve an accurate signal summation by compensating for not only the opamp input offset but also the signal mismatch error prestored in the column capacitor cell **231**. An appropriate switching sequence in combination with a feedback capacitor **251** (CC1), an extra capacitor **252** (CC2), and a clamp circuit **221** at the input of source follower **222** is used to autonomously accomplish this self-calibration process in the column integrator **240** at the beginning of each frame.

The self-calibration process is preferably carried out in the following four steps: reset, sampling, reset prior to integration, and signal integration. In the reset phase, the mismatch signal ΔV is sampled on to the memory capacitor cell **231** by switching on the transistor switch **224** (SW1). Transistor switches **242**(SW3), **246** (SW7), and **247** (SW8) are turned at the same time, resulting in an effective circuit as shown in FIG. **3a**. For simplicity of discussion, it is assumed that the common voltage $V_c=0$. At the end of the reset phase, the voltages at the input and output ports of the opamp **250** are $V_- = V_+ = V_o = V_{os}$, wherein V_{os} is the offset voltage of the opamp **250**. In the sampling phase, the calibration proceeds to switch off transistor switches **242** (SW3), **247** (SW8), and **244** (SW5) and turning on the transistor switches **245** (SW6) and **241**(SW2). FIG. **3b** shows the equivalent circuit of the integrator **240** in the sampling phase. Conservation of charges in the above two phases dictates that:

$$C_{CM}\Delta V + C_{CC1} \cdot V_{os} = C_{CM} \cdot V_- + C_{CC1} \cdot (V_- - V_o). \quad (1)$$

Assuming $C_{CM} = C_{CC1} = C$ and substituting $V_- = V_+ = V_{os}$, the calibration voltage at the output, $V_{o,c}$, can be expressed as

$$V_{o,c} = V_{os} - \Delta V. \quad (2)$$

This voltage is sampled onto the effective load capacitance **302** (CL) at the sampling phase with a relative polarity shown in FIG. **3b**.

Next, a second reset is carried out as shown. By turning off transistor switches **245** (SW6) and **246** (SW7) and turning on transistor switch **247** (SW8), the capacitor **302** (CL) is connected to the non-inverting input of the opamp **250** with the flipped polarity. The voltages at the input ports

of the opamp **250** become $V_+ = V_{os} - V_{o,c} = \Delta V$. The amplifier is reset again by switching on transistor switch **242** (SW3), resulting in an initial output voltage $V_{o,i} = V_- = V_+ = \Delta V$. FIG. **3c** shows the equivalent circuit. At the same time, an input voltage $V_{in,1}$ is sampled onto the memory capacitor cell **231** along with the error voltage ΔV .

The equivalent circuit for the final integration phase is shown in FIG. **3d**. The charge transfer can be expressed in the following equation:

$$C \cdot (V_{in,1} + \Delta V) = C \cdot V_{o,1} + C \cdot (V_- - V_{o,1}), \quad (3)$$

wherein $V_{o,1}$ is the output voltage of the integration:

$$V_{o,1} = 2V_- - (V_{in,1} + \Delta V) = \Delta V - V_{in,1}. \quad (4)$$

The switching sequence for the self-calibration is illustrated in FIGS. **4a-4j**.

The above self-calibration is for a first input signal $V_{in,1}$. For a subsequent integration step with an input signal $V_{in,2}$, the corresponding output voltage after an identical switching sequence can be expressed as

$$\begin{aligned} V_{o,2} &= 2V_- - (V_{in,2} + \Delta V) - (V_- + V_{in,1} - \Delta V) \\ &= \Delta V - (V_{in,1} + V_{in,2}). \end{aligned} \quad (5)$$

In general, the output voltage after nth step of integration is

$$V_{o,n} = \Delta V - \sum_{i=1}^n V_{in,i}. \quad (6)$$

Clearly, the offset V_{os} of the opamp is eliminated from the integration process. The residual mismatch error ΔV is further eliminated by an extra clamp circuit **253** (FIG. **2**) as the column integrator **240** resets prior to the integration by the output integrator **170**. Therefore, a linear summation of the photon-induced signal from the active pixels in the APS array **110** (e.g., **210**) is achieved with the preferred column integrator **240**.

Programmable resolution readout follows the self-calibration. With transistor switches **241**(SW2) and **248** (SW9) on, the column integrator **240** is reset by turning on **242**(SW3) momentarily. At the same time, the clamp circuit **221** is turned on by switching on the transistor switch **253**(CLP1) to sample the clamped reset level of the integrator onto the column memory capacitor **260** at the output of the integrator **240**. The switch **232** for selecting columns in each column is then turned on consecutively by the memory row decoder **132** for up to n rows if the kernel size is determined to be a square patch of $n \times n$ by the resolution control circuit. The signal from n rows are summed by the column integrator **140** and stored in the column memory array **150**. Next, the transistor switch **248**(SW9) is deactivated, and n consecutive columns are scanned after each reset of the output integrator **170** to add the signal from each kernel of n columns by an operation of the column select circuit **160**. After all columns have been scanned, the next n rows are summed up in the same fashion. A full frame is read out after all the rows have been processed. Clock diagrams in FIGS. **5a-5g** show the above-described sequence for a programmable resolution readout process.

For an APS array with $m \times m$ elements, the resolution of the output image with a square kernel of $n \times n$ pixels is given by $(m/n) \times (m/n)$. Hence, the resolution is programmable by varying the kernel size n based on the illumination condition. The signal-to-noise ratio of the output image is

enhanced by n times while the spatial resolution thereof is reduced by n times. In addition, the output signal level is increased by a factor of n^2 .

An embodiment of the APS image sensor in accordance with the present invention has 32×32 pixels. The sensor can be fabricated by a CMOS process using $1.2 \mu\text{m}$ n-well single poly and double metal with a linear capacitor option. The APS sensor pixel size is about $24 \mu\text{m} \times 24 \mu\text{m}$. The frame memory cell pixel size may be approximately $24 \mu\text{m} \times 28 \mu\text{m}$. The shape of each pixel cell in the frame memory may be slightly rectangular (i.e., the dimension along the column is longer) to achieve a memory capacitance of about 0.5 pf. The column integrators may be about 0.4 mm in a column pitch of about $24 \mu\text{m}$. A double metal process, "metal II", is used in layout for column parallel routing because of the limited column width. Metal II is also used for light shield wherever possible in the frame memory array and column processing circuits. The total dye size of the chip may be approximately $2.8 \text{ mm} \times 4.5 \text{ mm}$.

TABLE 1

Summary of Test Results	
Integrator linearity:	better than 8 bits for 1 V swing
Sensor saturation:	1 V
Conversion gain:	$6 \mu\text{V}/e$
Power consumptions:	1.58 mW @ 400 Frames/sec.
FPN with calibration:	15 mV
FPN without calibration:	40 mV
Memory leakage:	not observable in 1 second

Eighteen out of twenty-four fabricated parts that were tested worked properly without any defective pixels. Table 1 summarizes the test results. The linearity of both the column and the output integrators was better than about 8 bit in 1 V swing. The sensor had about 1 V signal saturation which was mainly limited by the dynamic range of the sensor pixel source-follower. The frame memory array had no observable leakage up to about 1 second. Total power consumption of the chip at a frame rate of 400 Hz was measured to be about 1.58 mW.

FIG. 6 shows an image with full resolution taken at 100 kPixels/sec with the tested sensor. With an error calibration activated, the column-wise fixed pattern noise (FPN) at full resolution was about 15 mV. This FPN did not increase as the signals from neighboring pixels were integrated. The residue FPN was found to be caused by the non-uniform charge injection. With the error calibration deactivated, the FPN was about 40 mV at full resolution.

FIGS. 7a and 7b demonstrate the signal enhancement when integration kernel changes from 1×1 pixels to 2×2 pixels with the same frame integration time. Much better image quality is achieved with the FPN calibration (FIG. 7a) than without the FPN calibration (FIG. 7b). At the lower resolution, a clear picture is achieved for an image hardly recognizable at the full resolution. FIGS. 8a and 8b show the detailed measurement, at a uniform illumination, of the signal (FIG. 8a) and the signal-to-noise ratio enhancement (FIG. 8b) as the summation kernel changes from 1×1 pixels to 4×4 pixels. A 60-mV signal from the single pixels is summed up to about 940 mV. The signal-to-noise ratio is enhanced following the square root rule as signals from different rows are summed.

One unique aspect of the present invention is its light adaptive imaging. In particular, the preferred APS image sensor can autonomously and dynamically adjust the spatial resolution of the output image therefrom to maintain a desired magnitude for an output signal in each output pixel

according to the conditions of a targeted object. Specifically, as the illumination, i.e., incoming radiation from the object, becomes insufficient (i.e., below a threshold level) in maintaining a desired signal-to-noise ratio for a selected output image resolution with a given kernel size, the preferred APS image sensor will attempt to maintain the desired signal-to-noise ratio and enhance the output signal level by reducing the resolution of the output image with a properly increased kernel size. Conversely, if the illumination of the targeted object increases above the threshold level for the selected output resolution, the preferred APS image sensor will attempt to increase the output resolution while maintaining the reduced signal-to-noise ratio at the desired level by reducing the kernel size.

Furthermore, this light adaptive imaging capability of the present invention allows for optimized imaging of a targeted object that moves with respect to the image sensor. One example of such an application is the imaging of a fixed target with an image sensor on aircraft or spacecraft.

Since the aperture of the image sensor is usually fixed and the distance between the targeted object and the image sensor changes, both the field of view of the image sensor and the view angle of the object change with the target distance. If the aircraft or spacecraft is far away from the targeted object, the field of view and the view angle are small. This means the received amount of light emitted by the object is small and the needed resolution for truthfully capturing the target image becomes low. The preferred APS image sensor can operate with a reduced output resolution by increasing the kernel size. This enhances the image brightness and the signal-to-noise ratio without sacrificing any image details of the targeted object. As the aircraft or spacecraft approaches the targeted object, the field of view increases and thereby the captured light from the object increases accordingly. Meanwhile, the view angle of the object increases and it is desirable to increase the output resolution of the image sensor for more detailed feature information of the object that is now available since the object is closer. Therefore, the preferred APS image sensor can reduce the kernel size to increase the output resolution while maintaining a sufficient brightness of the image with a signal-to-noise ratio above the threshold level.

The inventors further recognized that the sensor of the present invention can be used for time delay integration ("TDI"). A sensor in accordance with the invention can effectively function as an TDI sensor by feeding the column integrated signal back to the memory array so that the signal can be summed with the data from a subsequent frame, with a time delay. This TDI signal processing may be used in a situation where the image sensor and a target object have a relative motion with respect to each other so that captured images in two sequential frames of the target object are shifted on the image sensor. For example, a feature of the object that is captured on the k th row in one frame may be captured on the $(k+2)$ th row in a subsequent frame due to the relative motion. Accordingly, the signal in the k th row of the first frame will be added with the signal in the $(k+2)$ th row of the second frame in summing the signals of the two frames in a TDI process.

Although the present invention has been described in detail with reference to one embodiment, one ordinarily skilled in the art to which this invention pertains will appreciate that various modifications and enhancements may be made without departing from the scope and spirit of the present invention.

For example, any other image sensor, other than an APS array, may be used in practicing the present invention. In

general, any voltage or charge mode readout sensor array may be used with the same scheme and circuits having the same functionality. Some examples of such image sensors include an CCD array sensor, a photodiode array sensor, a charge injection image sensor, and a hybrid focal plane array sensor. Also, the scheme disclosed herein can be used in all situations wherein signal integration is performed.

Different type of amplifiers and integrators rather than those disclosed above can be adopted in practicing the present invention.

Although the preferred sensor can be advantageous in light adaptive imaging applications, the sensor may also be used as a regular analog readout sensor when operating in a single resolution mode.

In addition, any shape of pixel patches rather than a square shape may be used for a summation kernel, including a rectangular patch of pixels with m by n pixels ($m \neq n$).

These and other variations are intended to be encompassed by the following claims.

What is claimed is:

1. An image sensor for imaging an object, comprising:
 - a light sensing array configured to receive an input image of said object, said light sensing array having a plurality of detector pixels, said detector pixels arranged with respect to one another to form a plurality of columns and a plurality of rows;
 - a frame memory array formed on a substrate with said light sensing array and configured to store radiation-induced signals produced by said light sensing array indicative of said input image, said frame memory array having a plurality of memory cells, each said memory cell corresponding to one of said detector pixels;
 - a signal processor formed on said substrate with said frame memory and configured to process signals from said frame memory array to produce an output image with a prespecified signal magnitude and signal-to-noise ratio; and
 - a control circuit arranged and configured to control said light sensing array, said frame memory array and said signal processor.
2. An image sensor as in claim 1, further comprising a column buffer array integrated with said light sensing array, said column buffer array operable to receive signals from one column of said detector pixels and generate said radiation-induced signals to be stored in said frame memory array.
3. An image sensor as in claim 1, further comprising:
 - a sensor row decoder integrated with said light sensing array for addressing and selecting at least one row of said detector pixels;
 - a memory row detector integrated with said frame memory array for addressing and selecting at least one row of said memory cells;
 - a column integrator array in said signal processor, said column integrator array having a plurality of integrating circuits each connected to one of said columns in said frame memory for signal summation over selected rows set by said memory row decoder;
 - a column selector in said signal processor for selecting at least one column of said frame memory cells; and
 - an output integrator in said signal processor for signal summation over column signals from said column integrator array that are selected by said column selector.
4. An image sensor as in claim 3, wherein said signal processor is operable to add signals from a certain number

of neighboring memory cells to produce a signal with an increased magnitude and an improved signal-to-noise ratio.

5. An image sensor as in claim 4, wherein said certain number of neighboring memory cells is determined by comparing said radiation-induced signals with a plurality of prespecified threshold signals.

6. An image sensor as in claim 4, wherein said certain number of neighboring memory cells dynamically changes with the brightness of said input image based on an operation of said control circuit.

7. An image sensor as in claim 4, wherein said certain number of neighboring memory cells dynamically changes with a distance between said light sensing array and said object based on an operation of said control circuit.

8. An image sensor as in claim 3, wherein said column integrator array is operable to minimize a column-wise fixed pattern noise.

9. An image sensor as in claim 3, wherein output terminals of said column integrator array are connected to each column of said frame memory array, said control circuit operable to feed integrated output signals from said column integrator array back to said frame memory array in a time delay integration.

10. An image sensor as in claim 1, wherein said light sensing array is selected from a group consisting of an active pixel sensor array, an CCD array, a photodiode array, a charge injection image sensor, and a hybrid focal plane array sensor.

11. An integrated sensor with a programmable resolution, comprising:

- a light sensing array having a plurality of sensing pixels that are arranged with respect to one another to form a plurality of columns and a plurality of rows, said light sensing array having a sensor row decoder addressing and selecting at least one row of said sensing pixels;
 - a frame memory array for storing radiation-induced signals that are produced by said light sensing array, said frame memory array having a plurality of memory cells each corresponding to one of said sensing pixels and a memory row detector for addressing and selecting at least one row of said memory cells;
 - a column integrator array having a plurality of integrating circuits each connected to one of said columns in said frame memory;
 - a column memory array having column memory cells for receiving signals from said integrating circuits;
 - a column selector configured to select at least one column of said frame memory cells;
 - an output integrator configured to integrate column signals from said column integrator array that are selected by said column selector; and
 - a control circuit configured to control said light sensing array, said frame memory array, said column integrator, said column selector, and said output integrator to produce an output image satisfying a signal magnitude criterion and a signal-to-noise ratio criterion based on an adjustment of the resolution of said output image.
12. A sensor as in claim 11, wherein said light sensing array is an active pixel sensor array wherein each of said sensing pixels has a photogate and a pixel circuit formed on a substrate.
13. A sensor as in claim 12, wherein said pixel circuit includes a transfer gate and a first transistor source follower disposed on said substrate, said transfer gate configured to relay a signal from said photogate to said first source follower.

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14. A sensor as in claim **11**, further comprising a column buffer array electrically connected between said light sensing array and said frame memory array, said column buffer array having an array of buffer cells each corresponding to and shared by sensing pixels in one of said columns in said light sensing array.

15. A sensor as in claim **14**, wherein each of said buffer cells includes an AC-coupled follower whose input terminal is clamped to a prespecified voltage and is configured to generate one of said radiation-induced signals by a clocked action of resetting and sampling that is controlled by said control circuit.

16. A sensor as in claim **11**, wherein each of said memory cells comprises a memory capacitor and a switch transistor.

17. A sensor as in claim **11**, wherein each of said integrating circuits in said column integrator array is a switched-capacitor integrator which is capable of compensating for a column-wise fixed pattern noise according to a clocked switching sequence controlled by said control circuit.

18. A sensor as in claim **11**, further comprising a resolution control circuit connected to said light sensing array, said resolution control circuit configured to compare signals from said sensing pixels to a plurality of different prespecified threshold levels to determine a size of a summation kernel, comprising neighboring sensing pixels, for a subsequent signal processing so that signals from the pixels in said summation kernel are summed as an output signal.

19. A sensor as in claim **18**, wherein said resolution control circuit comprises a plurality of signal comparators

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connected in parallel, each of said signal comparators having a different prespecified threshold value and connected to a digital counter and decoder for generating a command for controlling a resolution.

20. A method for performing light adaptive imaging with an image sensor having a sensor array of sensing pixels arranged in columns and rows, comprising:

capturing a first frame indicative of an image of an object sensed by said sensing pixels;

saving said first frame in a frame memory;

comparing signal magnitudes of said sensed pixels in said first frame with a predetermined threshold value;

determining a first number of sensing pixels in a first summation kernel consisting of neighboring pixels according to a result of said comparing;

capturing a second frame indicative of an image of said object;

saving said second frame in said frame memory;

dividing said sensor array into a plurality of components with each component being said summation kernel with said first number of sensing pixels; and

adding signals of said sensing pixels in said summation kernel to generate a resolution-reduced array of signals indicative of said second frame with an improved signal-to-noise ratio and an increased signal magnitude.

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